

Silicon PNP Power Transistors

2SA1021

DESCRIPTION

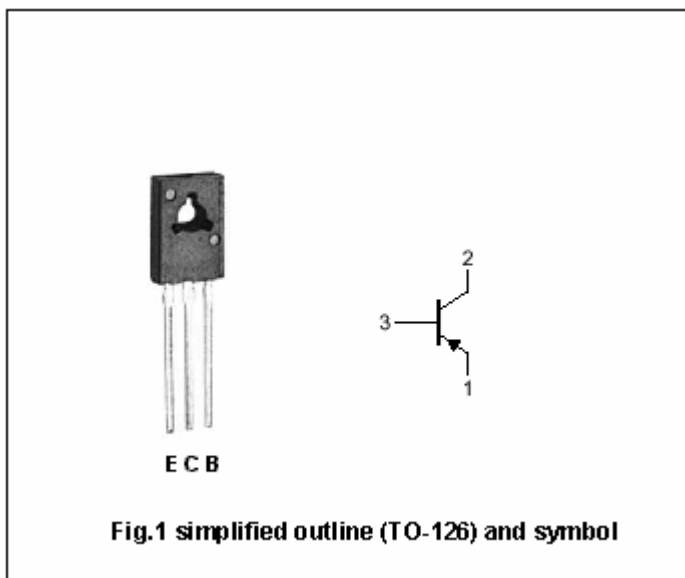
- With TO-126 package
- High breakdown voltage
- Large current capacity

APPLICATIONS

- For color TV sound output;converters  
Inverters applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CB0</sub>	Collector-base voltage	Open emitter	-150	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	-150	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-6	V
I <sub>C</sub>	Collector current		-1.5	A
I <sub>CM</sub>	Collector current-Peak		-2.5	A
P <sub>C</sub>	Collector power dissipation	T <sub>a</sub> =25°C	1.0	W
		T <sub>C</sub> =25°C	20	
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-1mA; R <sub>BE</sub> =∞		-150		V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =-10μA; I <sub>E</sub> =0		-150		V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =-10μA; I <sub>C</sub> =0		-6		V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-500mA; I <sub>B</sub> =-50mA			-0.5	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-500mA; I <sub>B</sub> =-50mA			-1.2	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-120V; I <sub>E</sub> =0			-1.0	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-4V; I <sub>C</sub> =0			-1.0	μA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-150mA; V <sub>CE</sub> =-5V	60		320	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-50mA; V <sub>CE</sub> =-10V	15			MHz

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PACKAGE OUTLINE

